

SEMISTACK

Antiparallel thyristors for softstart

SKKQ 430

Features

- · Compact design
- . Thyristor with amplifying gate
- Pressure contact technology

Typical Applications

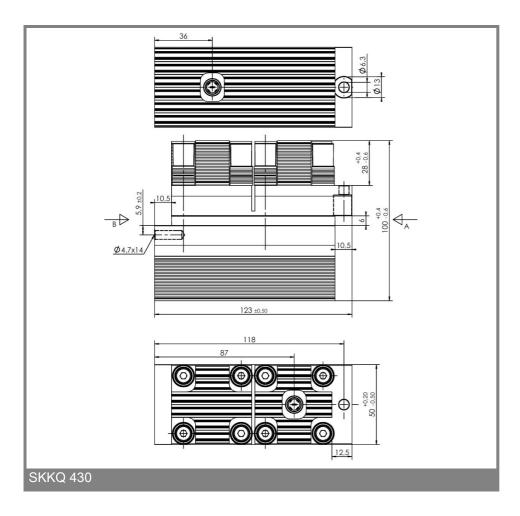
Soft Starters

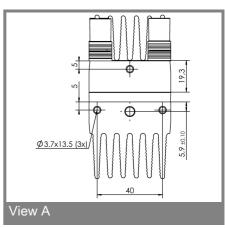
 T_{vjmax} up to 150°C is allowable for overload conditions, max. time period for the overload condition is 25s.

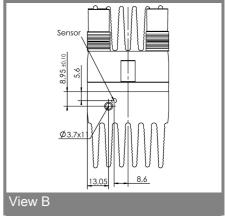
Absolute Maximum Ratings							
Symbol	Conditions	Values	Units				
loverload	W1C; sin. 180°; 20 sec.; T _{vimax.} = 150 °C; T _{vistart} = 40°C	1500	Α				
I _{TSM}	$T_{vj} = 25^{\circ}C; 10 \text{ ms}$	17000	Α				
	$T_{vj} = 125^{\circ}C; 10 \text{ ms}$	15000	Α				
I²t	T _{vj} = 25°C; 8,3 10 ms	1445000	A²s				
	T _{vj} = 125°C; 8,3 10 ms	1125000	A²s				
SKKQ 430/14							
V_{RSM}		1500	V				
V_{RRM}, V_{DRM}		1400	V				
SKKQ 430/18							
V_{RSM}		1900	V				
V_{RRM}, V_{DRM}		1800	V				
T _{vj}		-40 +125 ¹⁾	°C				
T _{stg}		-40 + 125	°C				

Characteristics						
Symbol	Conditions	min.	typ.	max.	Units	
V_T	$T_{vi} = 25^{\circ}C; I_{T} = 1700 A$			1,5	V	
$V_{T(TO)}$	T _{vj} = 125°C			0,85	V	
r _T	T _{vj} = 125°C			0,3	mΩ	
$I_{DD};I_{RD}$	T_{vj} = 125°C; V_{RD} = V_{RRM} ; per module			180	mA	
t _{gd}	$T_{vj} = 25^{\circ}C; I_{G} = 1A; di_{G}/dt = 1A/\mu s$		1		μs	
t _{gr}	$V_{D} = 0.67 * V_{DRM}$		2		μs	
(dv/dt) _{cr}	T _{vi} = 125°C		1000		V/µs	
(di/dt) _{cr}	T _{vi} = 125°C; f = 50 60 Hz		200		A/µs	
t _q	T _{vi} = 125°C		200		μs	
I _H	$T_{vj} = 25^{\circ}C$		150	500	mA	
IL	$T_{vj} = 25^{\circ}C; R_{G} = 33 \Omega$		300	2000	mA	
V _{GT}	T _{vi} = 25°C; d.c.	3			V	
I _{GT}	$T_{vj} = 25^{\circ}C; d.c.$	200			mA	
V_{GD}	$T_{vi} = 125^{\circ}C$; d.c.			0,25	V	
I_{GD}	$T_{vj} = 125^{\circ}C; d.c.$			10	mA	
R _{th(j-s)}	cont.; per thyristor			0,037	K/W	
M _t			5 ± 15%		Nm	
m	approx.		1200		g	
Case			SKKQ 430			









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